

High-voltage Amplifier Transistor

(-120V, -50mA)

2SA1579 / 2SA1514K / 2SA1038S

●Features

- 1) High breakdown voltage. ($BV_{CEO} = -120V$)
- 2) Complements the 2SC4102 / 2SC3906K / 2SC2389S.

●Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Collector power dissipation	P _c	0.2	W
		0.3	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

●Packaging specifications and hFE

Type	2SA1579	2SA1514K	2SA1038S
Package	UMT3	SMT3	SPT
hFE	RS	RS	RS
Marking	R*	R*	-
Code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000

*Denotes hfc

●External dimensions (Units : mm)

2SA1579

ROHM : UMT3 (1) Emitter
EIAJ : SC-70 (2) Base
JEDEC : SOT-323 (3) Collector

2SA1514K

ROHM : SMT3 (1) Emitter
EIAJ : SC-59 (2) Base
JEDEC : SOT-346 (3) Collector

2SA1038S

ROHM : SPT (1) Emitter
EIAJ : SC-72 (2) Collector
(3) Base

●Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-120	-	-	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-120	-	-	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	-5	-	-	V	$I_E = -50\mu A$
Collector cutoff current	I_{CBO}	-	-	-0.5	μA	$V_{CB} = -100V$
Emitter cutoff current	I_{EBO}	-	-	-0.5	μA	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	$I_C/I_E = -10mA/-1mA$
DC current transfer ratio	hFE	180	-	560	-	$V_{CE} = -6V, I_C = -2mA$
Transition frequency	f _r	-	140	-	MHz	$V_{CE} = -12V, I_E = 2mA, f = 30MHz$
Output capacitance	C _{ob}	-	3.2	-	pF	$V_{CB} = -12V, I_E = 0A, f = 1MHz$

单击下面可查看定价，库存，交付和生命周期等信息

[>>ROHM Semiconductor\(罗姆\)](#)